Abstracts

InAlAs/InGaAs/InP-HEMT Technologies for High-Yield Analog/Digital ICS

Y. Umeda, T. Enoki, K. Osafune, H. Ito and Y. Ishii. "InAlAs/InGaAs/InP-HEMT Technologies for High-Yield Analog/Digital ICS." 1996 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 98. (1996 [MCS]): 115-118.

High-yield and high-performance digital/analog ICs have been fabricated using the same InAlAs/InGaAs/InP-HEMT process. SCFL static frequency dividers show a fabrication yield of 63% and operate at 36.7 ±0.55 GHz. Two-stage MMIC-LNAs show a yield of 75% and at 62 GHz a noise figure of 4.3 ±0.19 dB and a gain of 11.8 ±0.25 dB.

❑ Return to main document.